Silicon NPN Power Transistors 2SD325

DESCRIPTION

- With TO-220C package
- Complement to type 2SB511
- Low collector saturation voltage

APPLICATIONS

- Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

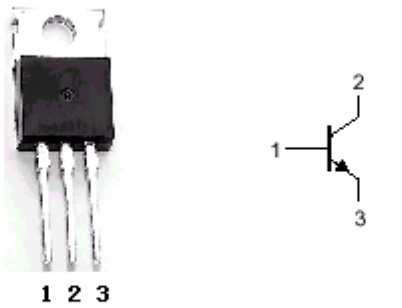

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	35	V
V_{CEO}	Collector-emitter voltage	Open base	35	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_{CM}	Collector current -peak		3.0	A
P_C	Collector dissipation	T_a=25℃	1.75	W
		T_C=25℃	10	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-50~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA; I_B=0	35			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1.5A; I_B=0.15A			1.0	V
V_{BE}	Base-emitter on voltage	I_C=1A ; V_{CE}=5V			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=20V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=4V; I_C=0			1.0	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=2V	40		320	
h_{FE-2}	DC current gain	I_C=0.1A ; V_{CE}=2V	35			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=5V		8		MHz

◆ **h_{FE-1} Classifications**

C	D	E	F
40-80	60-120	100-200	160-320

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PACKAGE OUTLINE

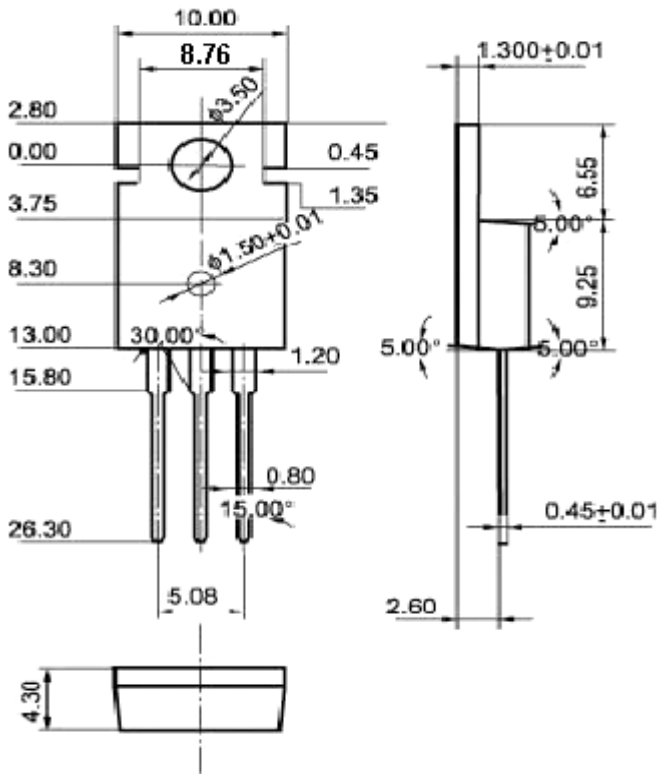

Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)